

CAB4A - DDR4 寄存器

32 位 1:2 命令/地址/控制缓冲器和 1:4 差分时钟缓冲器

查询样品: CAB4A

特性

- 符合 DDR4RCD01 JEDEC 标准
- DDR4 带寄存器的双列直插内存模块 (RDIMM) 和 低负载双列直插内存模块 (LRDIMM) 高达 DDR4-2400
- 32 位 1 至 2 寄存器输出
- 1至4差分时钟缓冲器
- 1.2V 运行
- 具有内部反馈的锁相环 (PLL)
- 可配置驱动器强度
- 可扩展弱驱动器
- 可编程延迟
- 输出驱动器校准
- 地址映射和倒置
- DDR4 完全奇偶校验运行
- 片载可编程 V_{REF} 生成
- CA 总线协商模式
- I²C™ 接口支持
- 多达 16 个用于支持三维堆叠 (3DS) RDIMM 和 LRDIMM 的逻辑模组
- 多达 4 个用于支持 RDIMM 和 LRDIMM 的物理模组

说明

CAB4 是一款 32 位 1:2 命令/地址/控制缓冲器和 1:4 差分时钟缓冲器,它被设计用于以 1.2V VDD 模式在 DDR4 带寄存器的 DIMM 上的运行。

所有输入是使用外部或内部电压基准的伪差分输入。 所有输出是满摆幅 CMOS 驱动器,此驱动器针对驱动 DDR4 RDIMM,LRDIMM 和 3D 堆叠 DIMM 应用中的 15Ω 至 50Ω 有效端接迹线而进行了优化。 时钟输出、 命令/地址输出、控制输出、数据缓冲控制输出可成组 启用,并且可采用单独的驱动强度,以补偿不同的 DIMM 网状拓扑结构。 DDR4 寄存器以不同的时钟频 率运行(CK_t 和 CK_c)。 输入在 CK_t 变为高电平 和 CK_c 变为低电平交叉点时被记录。 如果输入信号 DSC[n:0]_n 中的一个被驱动为低电平,输入信号可被 重新驱动至输出,或者它可在满足特定输入条件时被用 来访问器件内部控制寄存器。

此器件的特点是可在 -40°C 至 95°C 的温度范围内运

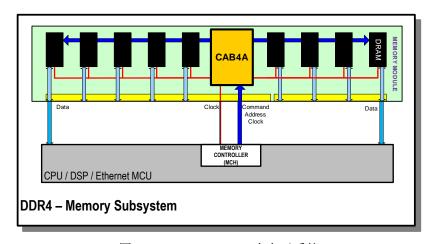


图 1. DDR4 - RDIMM 内存子系统

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FUNCTIONAL BLOCK DIAGRAM

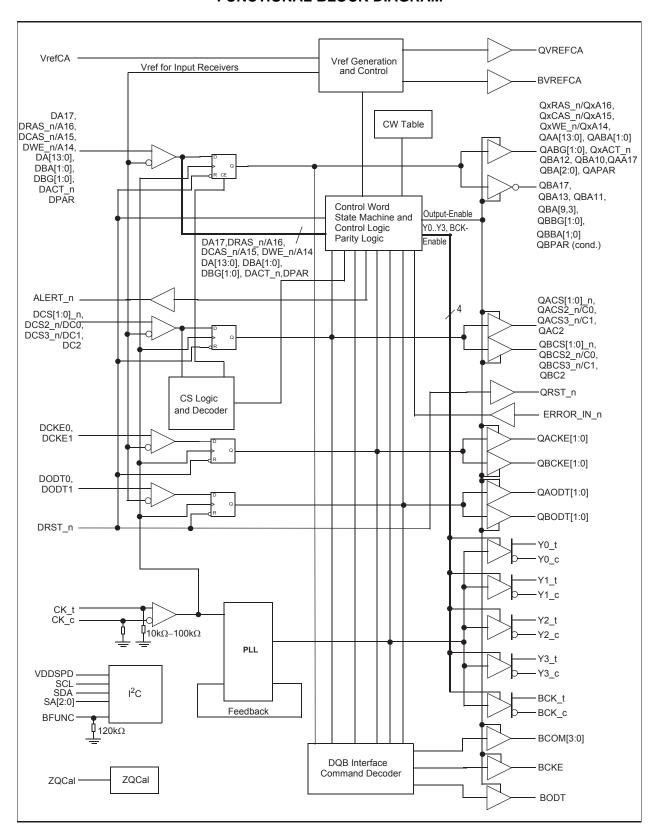




Table 1. TERMINAL FUNCTIONS

SIGNAL		TVDE	D.F.O.D.IDTION			
GROUP	NAME	TYPE	DESCRIPTION			
	DCKE0/1 DODT0/1		DRAM corresponding register function pins not associated with Chip Select.			
	DCS0_nDCS1_ n		DRAM corresponding register Chip Select signals.			
Input Control bus	DCS2_nDCS3_ n or DC0DC1	CMOS ⁽¹⁾ VREF based	DRAM corresponding register Chip Select signals. These pins initiate DRAM address/command decodes, and as such exactly one will be LOW when a valid address/command is present which should be re-driven. Some of these have alternative functions: DCS2_n ↔ DC0 DCS3_n ↔ DC1			
	DC2		DRAM corresponding register Chip ID 2 signal.			
Input Address and Command bus	DA0DA13, DA17 DBA0DBA1, DBG0DBG1 DA14DA16 or DWE_n, DCAS n,	CMOS ⁽¹⁾ VREF based	DRAM corresponding register inputs. In case of an ACT command some of these terminals have an alternative function: DRAM corresponding register command signals ■ DA14 ↔ DWE_n ■ DA15 ↔ DCAS_n ■ DA16 ↔ DRAS_n			
	DRAS_n					
	DACT_n		DRAM corresponding register DACT_n signal.			
Clock inputs	CK_t, CK_c	CMOS differential	Differential master clock input pair to the PLL with a 10 k Ω ~ 100 k Ω pull-down resistor.			
Reset input	DRST_n	CMOS input	Active LOW asynchronous reset input. When LOW, it causes a reset of the internal latches and disables the outputs, thereby forcing the outputs to float.			
Parity input	DPAR	CMOS ⁽²⁾ VREF based	Input parity is received on pin DPAR and should maintain even parity across the address and command inputs (see above), at the rising edge of the input clock.			
Error Input	ERROR_IN_n	CMOS input	DRAM address parity and CRC Alert is connected to this inp pin, which in turn is buffered and re-driven to the ALERT n output of the register. Requires external pull-up resistor. (3)			
	BODT		Data buffer on-die termination signal.			
	BCKE	CMOS ⁽³⁾	Data buffer clock enable signal for PLL power management.			
Data buffer control and communication outputs	BCOM[3:0]	CIVIOS	Register communication bus for data buffer programming and control access.			
	BCK_t, BCK_c	CMOS differential	Differential clock output pair to the data buffer			
	BVREFCA	VDD/2Reference Voltage	Output reference voltage for data buffer control bus receivers.			

⁽¹⁾ These receivers use VREFCA as the switching point reference.

These receivers use VREFCA as the switching point reference.
CMOS: These outputs with rail to rail signal swing and programmable impedance are optimized for memory applications to drive DRAM inputs over a terminated transmission line. Error_In_n: Internal Pull-up resistor can be turned on.



Table 1. TERMINAL FUNCTIONS (continued)

SIGN	IAL		PEOGRAPHICA			
GROUP	NAME	TYPE	DESCRIPTION			
Output Control Bus	QACKE0/1, QAODT0/1, QBCKE0/1, QBODT0/1		Register output CKE and ODT signals.			
	QACS0_nQACS 1_n, QBCS0_nQBCS 1_n		Register output Chip Select signals.			
	QACS2_nQACS 3_n, QBCS2_nQBCS 3_n or QAC0QAC1, QBC0QBC1		Register output Chip Select signals. These pins initiate DRAM address/command decodes, and as such exactly one will be LOW when a valid address/command is present which should be re-driven. Some of these have alternative functions (Chip ID): $ QxCS2_n \leftrightarrow QxC0 $ $ QxCS2_n \leftrightarrow QxC0 $			
	QAC2, QBC2		Register output Chip ID2 signals.			
Output Address and Command bus	QAA0QAA13, QAA17, QBA0QBA13, QBA17, QABA0QABA1, QBBA0QBBA1, QAG0QAG1, QBG0QBG1	CMOS	Outputs of the register, valid after the specified clock count ar immediately following a rising edge of the clock.			
	QAA14QAA16, QBA14QBA16 or QAWE_n, QACAS_n, QARAS_n, QBWE_n, QBCAS_n,		Outputs of the register, valid after the specified clock count and immediately following a rising edge of the clock. In case of an ACT command some of these terminals have an alternative function: ■ QxA14 ↔ QxWE_n ■ QxA15 ↔ QxCAS_n			
	QBRAS_n		 QxA16 ↔ QxRAS_n 			
	QAACT-n, QBACT_n		Outputs of the register, valid after the specified clock count an immediately following a rising edge of the clock.			
Vref output	QVREFCA	VDD/2 Reference voltage	Output reference voltage for DRAM receivers			
Clock outputs	Y0_tY3_t, Y0_cY3_c	CMOS differential	Re-driven clocks			
Reset output	QRST_n	CMOS	Re-driven reset. This is not an asynchronous output.			
Parity outputs	QAPAR, QBPAR	CMOS	Re-driven parity ⁽⁴⁾			
Error out	ALERT_n	Open drain	When LOW, this output indicates that a parity error was identified associated with the address and/or command inputs when parity checking is enabled or that the ERROR_IN_n input was asserted, regardless of whether parity checking is enabled or not.			
I ² C pins	SDA SCL SA[2:0] BFUNC VDDSPD	Open drain I/O CMOS input CMOS input CMOS input Power input	I ² C Data I ² C Clock I ² C Address signals Reserved ⁽⁵⁾ I ² C power input			

 I^2C inputs: These inputs are 2.5V inputs, except BFUNC which is a 1.2V input. BFUNC has an internal pull-down resistor of 120 $k\Omega$ to V.

⁽⁵⁾



Table 1. TERMINAL FUNCTIONS (continued)

SIGNAL		TVDE	DESCRIPTION		
GROUP	NAME	TYPE	DESCRIPTION		
	VREFCA	VCC/2Reference voltage	Input reference voltage for the CMOS inputs.		
	VDD	Power input	Power supply voltage		
	VSS	Ground input	Ground		
	AVDD	Analog power	Analog supply voltage		
Miscellaneous pins	PVDD	Clock power	Clock logic and clock output driver power supply.		
	PVSS	Clock ground	Clock logic and clock output driver ground.		
	ZQCAL	Reference	Needs a calibration resistor of 240Ω ±1% to VSS.		
	NU	Mechanical ball	Do not connect on PCB.		
	RFU[3:0]	I/O	Reserved; must be left floating on DIMM and in DDR4 register.		



修订历史记录

将文档更改为生产数据。

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PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
							(6)				
CAB4AZNRR	LIFEBUY	NFBGA	ZNR	253	2000	RoHS & Green	SNAGCU	Level-3-260C-168 HR	-40 to 95	CAB4A6	

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

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- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

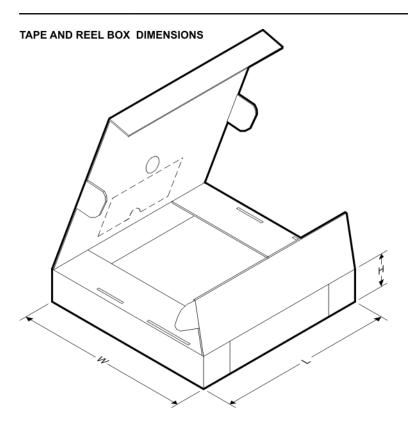
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CAB4AZNRR	NFBGA	ZNR	253	2000	330.0	24.4	8.3	13.8	1.8	12.0	24.0	Q1

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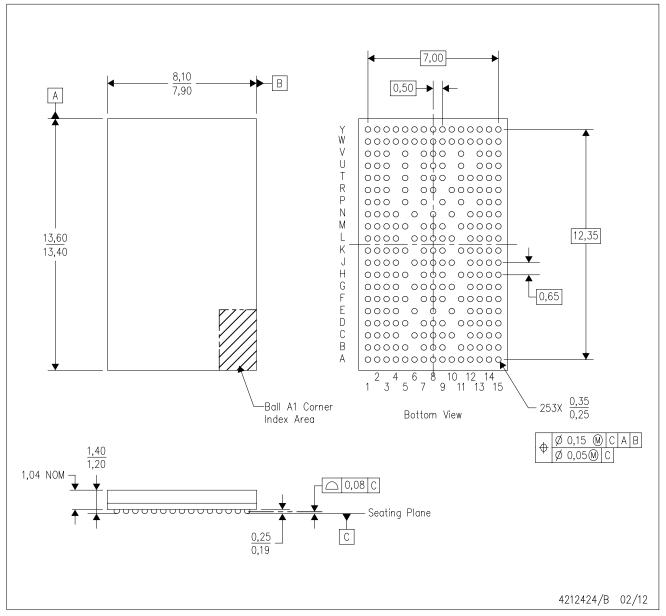


*All dimensions are nominal

Device	Device Package Type		Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
CAB4AZNRR	NFBGA	ZNR	253	2000	367.0	367.0	38.0	

ZNR (R-PBGA-N253)

PLASTIC BALL GRID ARRAY



NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. This package is Pb-free.



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